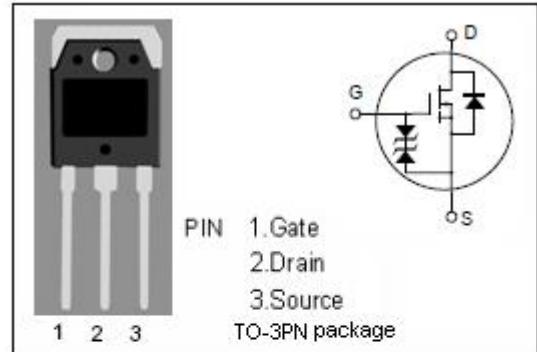


isc N-Channel MOSFET Transistor

2SK2398

DESCRIPTION

- Drain Current $I_D = 45A @ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 60V$ (Min)
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

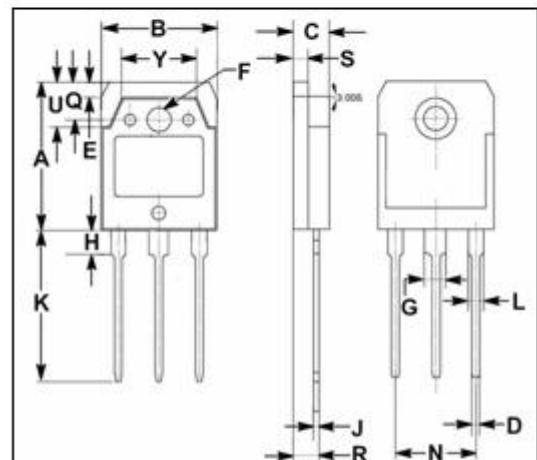
- Switching regulators
- UPS
- DC-DC converters
- General purpose power amplifier

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	60	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $T_C=25^\circ C$	45	A
$I_{D(puls)}$	Pulsed Drain Current	180	A
P_{tot}	Total Dissipation@ $T_C=25^\circ C$	100	W
T_j	Max. Operating Junction Temperature	150	°C
T_{stg}	Storage Temperature Range	-55~150	°C

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.25	°C/W
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	50	°C/W



DIM	mm	
	MIN	MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

isc N-Channel Mosfet Transistor

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• ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0$; $I_D=10\text{mA}$	60			V
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=10\text{V}$; $I_D=1\text{mA}$	1.5		3.0	V
V_{SD}	Diode Forward on-Voltage	$I_S=45\text{A}$; $V_{\text{GS}}=0$			1.8	V
$R_{\text{DS}(\text{on})}$	Drain-Source On-Resistance	$V_{\text{GS}}=10\text{V}$; $I_D=25\text{A}$			0.03	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{\text{GS}}= \pm 16\text{V}$; $V_{\text{DS}}=0$			± 10	μA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=60\text{V}$; $V_{\text{GS}}=0$			100	μA
C_{iss}	Input Capacitance	$V_{\text{DS}}=25\text{V}$; $V_{\text{GS}}=0\text{V}$; $f_T=1\text{MHz}$		1800		pF
C_{rss}	Reverse Transfer Capacitance			350		
C_{oss}	Output Capacitance			900		
t_r	Rise Time	$V_{\text{GS}}=10\text{V}$; $I_D=25\text{A}$; $V_{\text{DD}}=30\text{V}$; $R_L=1.2\ \Omega$		20		ns
t_{on}	Turn-on Time			30		
t_f	Fall Time			40		
t_{off}	Turn-off Time			130		

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